

Electronic Materials and Photonics

Room 207 A W - Session EM1+AP+CA+CPS+MS+TF-WeM

Advances in Wide Bandgap Materials and Devices

Moderator: Erin Cleveland, Laboratory of Physical Sciences

8:00am **EM1+AP+CA+CPS+MS+TF-WeM-1 Progress in Wide and Ultra-Wide Bandgap Semiconductors – Energy Implications, John Muth**, North Carolina State University

INVITED

The progress in developing wide bandgap semiconductors from idea to commercial products over the past 30 years is one of the great successes of interdisciplinary research between materials, science, physics and electrical engineering. Presently, we are experiencing another step change in the performance of semiconductor devices as ultra-wide bandgap materials (Diamond, Aluminum Nitride, Gallium Oxide) overcome fundamental issues like wafer size, the ability to control conductivity with doping in controlled ways and techniques like wafer bonding become more widely used and high voltage device demonstrations are being made. Similarly, SiC and Gallium Nitride wide bandgap devices are leveraging more mature fabrication technologies including deep ion implantation, sophisticated etching techniques, and high k dielectrics to enable non-planar device geometries, that lower the on resistances and provide increased breakdown voltages. The use of emerging alloys like AlScN offer higher performance higher frequency transistors as well as an addition route to integrate ferroelectric materials with CMOS. Innovations in photonic devices should not be left out with microLEDs for displays and chip to chip communications and increased ability to make low loss visible photonic integrated circuits as well as narrow linewidth lasers for quantum. The goal of this presentation will be to put these advances into context comparing the advances in the different materials and their potential for energy savings for a variety of systems including Artificial Intelligence, Data Centers, and computing and systems where size, weight, power efficiency and reliability matter including ships, planes and satellites.

8:30am **EM1+AP+CA+CPS+MS+TF-WeM-3 Limitations and Effects of Heavy Metal Doping in GaN, J. Pierce Fix**, Montana State University; **Kevin Vallejo**, Idaho National Laboratory; **Nicholas Borys**, Montana State University; **Brelon May**, Idaho National Laboratory

The doping of third-party elements is the backbone of the microelectronics industry, as it allows delicate control of electron/hole concentration, but it can also be used to imbue a host matrix with unique magnetic or optical properties. Wurtzite gallium nitride is a widely studied large bandgap semiconductor. There are reports of doping GaN with numerous elements, with some being extensively employed in commercial applications. However, there are still a few elements which remain completely unexplored. This work investigates the doping limits and effects of select transition metals, lanthanoids, and actinoids in GaN. The structural, electronic, and optical properties of these first-of-a-kind combinations are presented. Embedding single crystal wide bandgap materials with additional functionality will provide building blocks for new multifunctional hybrid systems for novel sensors, quantum science, or meta-multiferroics. Leveraging the non-centrosymmetric piezoelectric host matrix and atomic-level control of dopant species could allow for active tuning of proximity and correlated phenomena, potentially opening the door for applications of actinide elements beyond nuclear fuels.

8:45am **EM1+AP+CA+CPS+MS+TF-WeM-4 Using Raman Spectroscopy to Characterize Stress and Strain in SiC, Michelle Sestak**, HORIBA

Raman spectroscopy is a useful, non-destructive tool for measuring stress and strain in materials like silicon carbide (SiC). In this study, we use Raman spectroscopy to analyze stress and strain in three types of SiC samples: as-cut, diamond-lapped, and after chemical mechanical polishing (CMP). By examining shifts in the Raman peak positions, we identify differences in residual stress caused by each processing step. The as-cut samples show high stress due to mechanical damage, while diamond-lapped samples show partial stress relief. The CMP-treated samples exhibit the lowest stress levels, indicating effective surface relaxation. These results demonstrate how Raman spectroscopy can be used to monitor and compare the effects of different surface preparation techniques on stress in SiC materials.

9:00am **EM1+AP+CA+CPS+MS+TF-WeM-5 Nanoscale GaN Vacuum Electron Devices, George Wang, Keshab Sapkota, Huu Nguyen, Gyorgy Vizkelethy**, Sandia National Laboratories

On-chip vacuum electron devices that operate by cold field emission have the potential to combine advantages of traditional vacuum electron devices (e.g. vacuum tubes), such as robustness in harsh environments and high frequency operation, together with those of modern solid-state devices, such as size and energy efficiency. By shrinking the vacuum or “air” channel to nanoscale dimensions well below the electron mean free path in air, such devices can operate at ambient pressures while maintaining the physical advantages of ballistic vacuum transport. Here, we present lateral gallium nitride (GaN) semiconductor nanogap field emission diodes and transistors that exhibit ultra-low turn-on voltage, high field-emission current, and that operate in air. The fabrication of these nanoscale devices is enabled by a two-step top-down etching approach allowing for the necessary sidewall verticality and surface smoothness. We present experimental and modeling results on the field emission characteristics of these devices at various nanogap sizes and operating pressures. Initial results showing the potential of these devices for radiation-hardened, photodetection and high-temperature applications will be presented. These results provide critical new insights into the behavior of this new class of devices and point to future challenges and opportunities. *Sandia National Laboratories is managed and operated by NTESS under DOE NNSA contract DE-NA0003525*

9:15am **EM1+AP+CA+CPS+MS+TF-WeM-6 Combining CVD of Graphene and SiC for Efficient Layer Transfer, Daniel Pennachio, Jenifer Hajzus, Rachael Myers-Ward**, US Naval Research Laboratory

Remote epitaxy (RE) is a thin film growth technique that incorporates a release layer into the material stack, allowing for transfer of the deposited material with minimal defects [1]. Transferred 2D two-dimensional (2D) material, such as graphene, is commonly used for a release layer, but the transfer step can degrade the film and increase process complexity. To avoid this, we examine *in situ* graphitic carbon growth on SiC substrates before subsequent SiC epitaxy in the same chemical vapor deposition (CVD) RE process. RE SiC and subsequent SiC epilayer transfer is desired since isolated SiC membranes are excellent for quantum photonics and SiC substrate reuse can provide significant cost savings. Despite these benefits, the high-temperature hydrogen-containing CVD environment can damage graphene, making RE difficult under standard SiC growth conditions [2].

This study established growth windows for *in situ* graphene via propane-based hot wall CVD. This propane-based graphene growth enables an efficient transition to subsequent SiC deposition using established SiC growth conditions since it shares a similar hydrogen ambient to standard SiC CVD. Growing at 1620 °C in 20 slm H₂ with 20 sccm propane flow produced predominantly monolayer (ML) graphene films on on-axis 6H-SiC(0001) substrates with minimal defects found in Raman spectral maps. Films grown on 4° off-axis 4H-SiC(0001) substrates were multilayer (6 ML) graphitic carbon despite experiencing the same conditions as the on-axis substrates. This optimized graphene growth condition was used for subsequent RE attempts to study the effect of SiC precursor dose, C/Si ratio, and growth rate on epilayer crystallinity and graphene barrier damage. SiC crystalline quality appeared correlated to growth rate, with lower growth rates producing smoother films with fewer polytype inclusions. Single-crystalline, polytype-pure SiC epilayers was achieved on 4° off-axis CVD graphene/4H-SiC(0001). Effects of initial SiC growth parameters on the graphitic carbon release layer were explored via cross-sectional transmission electron microscopy (TEM) and attempts at epilayer transfer. Some growth interfaces exhibited non-uniform multilayer graphitic carbon, motivating further study of this growth system to improve boundary uniformity and SiC epilayer quality.

[1] Kim, Y., Cruz, S., Lee, K. et al. Nature 544, 340–343 (2017).

[2] Pennachio, D. J., Hajzus, J. R., & Myers-Ward, R. L. JVST B, 43(2). (2025).

9:30am **EM1+AP+CA+CPS+MS+TF-WeM-7 Multiscale Modeling of Self-heating Effects in AlGaIn/GaN High Electron Mobility Transistors (HEMT), Jerry Comanescu**, National Institute of Standards and Technology; **Albert Davydov**, NIST-Gaithersburg; **Michael Shur**, Theiss Research, Inc.; **Tyler Gervasio**, Behrang Hamadani, Michael Lloyd, NIST-Gaithersburg

AlGaIn/GaN based High Electron Mobility Transistors have emerged as state-of-the-art devices in power and RF electronics because of the outstanding electronic properties of the AlGaIn/GaN heterostructure. The large breakdown field of GaN (3.3 MV/cm, 11 times higher than silicon) enables HEMT operation in the kV-range while the high mobility of the two-

dimensional electron gas at the AlGaIn/GaN interface ensures that HEMTs have a very low on-resistance. In addition, the wide bandgap of GaN makes HEMT devices particularly suitable for high-temperature, high-power, and high-current operations. However, unlike silicon-based devices, the performance of current GaN based devices falls significantly shorter than what is expected based on the outstanding properties of GaN material. This gap in performance is even larger when HEMT devices experience self-heating under high-power operation regime, which strongly affects the device lifetime and reliability. Therefore, understanding the high-temperature operation and the self-heating effect is critical for improving the device design. We report on self-heating effect in AlGaIn/GaN HEMTs. We interpret our measurement results using a new compact CAD self-heating model. The model is based on the Unified Charge Control Model (UCCM) and is in excellent agreement with the measured data. Our results allow for the identification of the material properties and device parameters primarily responsible for the temperature dependencies of the device characteristics. The measured temperature dependencies also reveal non-ideal effects related to charge trapping, including threshold voltage instability and current-voltage characteristic hysteresis. The model accounts for the temperature distribution inside the HEMT devices (e.g., distribution of temperature along the channel) which are evaluated by a combination of TCAD simulations, heat transfer finite element simulations, and experiments performed on commercial HEMT devices. The developed compact self-heating model augments TCAD simulations for the Device Technology Co-Optimization approach by linking the AlGaIn/GaN HEMT performance and design optimization to material and interface properties.

9:45am **EM1+AP+CA+CPS+MS+TF-WeM-8 Atomic Layer Deposition of High-k Oxide Layers on Aluminum Gallium Nitride: Insight from Time-Resolved Synchrotron Studies**, *Nishant Patel*, *Shreemoyee Chakraborty*, Lund University, Sweden; *Byeongchan So*, lund University, Sweden; *Minho Kim*, *Alexis Papamichail*, Linköping University, Sweden; *Rosemary Jones*, Max IV Laboratory, Sweden; *Erik Lind*, *Vanya Darakchieva*, **Rainer Timm**, Lund University, Sweden

Gallium nitride (GaN) and aluminum gallium nitride (AlGaIn) are the materials of choice for enabling power electronic devices with superior energy efficiency and very high switching frequency. Such devices are based on metal-oxide-semiconductor (MOS) stacks, where downscaling and leakage control require gate insulators with high dielectric constant, so-called high-k oxides, such as HfO_2 . However, device performance and especially switching frequencies are often limited by the low quality of the (Al)GaN/high-k interface. Atomic layer deposition (ALD) is typically used for the synthesis of ultrathin, conformal high-k layers, where the choice of oxide material, ALD parameters, and pre-ALD cleaning methods strongly influence film and interface quality. Many important details about the physics and chemistry of the interface formation still remain unknown. Furthermore, until now all efforts to explore the high-k oxide film formation are based on *ex situ* approaches, meaning that film deposition and characterization of the resulting interface occur in separate steps.

Here, we will present a first time-resolved investigation of the ALD reactions of HfO_2 on (Al)GaN. We have used synchrotron-based ambient-pressure X-ray photoelectron spectroscopy (AP-XPS) and implemented the ALD process in the AP-XPS setup at the MAX IV synchrotron facility. Thus, we succeeded in mapping surface chemistry and electronic properties *in situ* during subsequent ALD half-cycles, which consisted of the deposition of tetrakisdimethylamido-hafnium (TDMA-Hf) and water. We observed a rather inefficient first ALD cycle, compared to other semiconductor ALD reactions, which improved with increasing aluminum content. Thickness and chemical composition of the resulting Hf-oxide film varied significantly if the order of the precursors was changed (TDMA-Hf first or water first). Both observations are against the established ligand-exchange ALD model and highlight the importance of in-depth studies for improving the quality of high-k layers on (Al)GaN.

In addition, we have used XPS to systematically investigate the electronic properties and chemical composition of the interface between different (Al)GaN substrates and HfO_2 or Al_2O_3 high-k oxide films, for different ALD temperatures, where Al_2O_3 layers typically resulted in a more stoichiometric oxide film. The choice of pre-ALD cleaning methods was also found to be of importance, which can enhance ALD efficiency but also result in significant interface contamination. We will discuss how our structural results can be easily implemented to improve device performance.

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